# N-Channel 200-V (D-S) MOSFET

### **Key Features:**

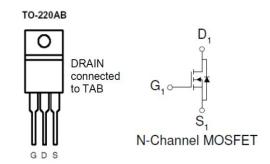
- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

Typical	<b>Applicatio</b>	ns:
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- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)	
200	40 @ V <sub>GS</sub> = 10V	130 <sup>a</sup>	
200	$46 @ V_{GS} = 6.5V$	130	





ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Units
Drain-Source Voltage		$V_{DS}$	200	V
Gate-Source Voltage		$V_{GS}$	±20	V
Continuous Drain Current a	T <sub>C</sub> =25°C	I <sub>D</sub>	130	Α
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	360	<b>A</b>
Continuous Source Current (Diode Conduction) a	T <sub>C</sub> =25°C	I <sub>S</sub>	90	Α
Power Dissipation <sup>a</sup>	T <sub>C</sub> =25°C	$P_{D}$	300	W
Operating Junction and Storage Temperature Range		$T_J,T_stg$	-55 to 175	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient <sup>c</sup>	$R_{\theta JA}$	62.5	°C/W
Maximum Junction-to-Case	$R_{\theta JC}$	1	C/VV

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#### Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature
- c. Surface Mounted on 1" x 1" FR4 Board.

#### **Electrical Characteristics**

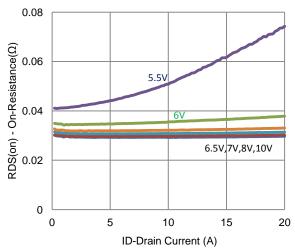
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
	Static					
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \text{ uA}$	2			V
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA
Zero Gate Voltage Drain Current		$V_{DS} = 160 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA
	I <sub>DSS</sub>	$V_{DS} = 160 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	160			Α
Drain-Source On-Resistance <sup>a</sup>	r	$V_{GS} = 10 \text{ V}, I_{D} = 10 \text{ A}$			40	mΩ
	r <sub>DS(on)</sub>	$V_{GS} = 6.5 \text{ V}, I_D = 8 \text{ A}$			46	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_{D} = 10 \text{ A}$		20		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = 45 \text{ A}, V_{GS} = 0 \text{ V}$		0.91		V
		Dynamic <sup>b</sup>				
Total Gate Charge	$Q_g$	$V_{DS} = 100 \text{ V}, V_{GS} = 6.5 \text{ V},$		94		
Gate-Source Charge	$Q_{gs}$	$v_{DS} = 100 \text{ v}, v_{GS} = 6.5 \text{ v},$ $I_{D} = 10 \text{ A}$		31		nC
Gate-Drain Charge	$Q_gd$	ID = 10 A		62		
Turn-On Delay Time	t <sub>d(on)</sub>	V - 100 V B - 10 O		48		
Rise Time	t <sub>r</sub>	$V_{DS} = 100 \text{ V}, R_L = 10 \Omega,$ $I_D = 10 \text{ A},$ $V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		63		ne
Turn-Off Delay Time	$t_{d(off)}$			171		ns
Fall Time	t <sub>f</sub>			51		
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V, f = 1 Mhz		9659		
Output Capacitance	C <sub>oss</sub>			419		pF
Reverse Transfer Capacitance	$C_{rss}$			331		

#### Notes

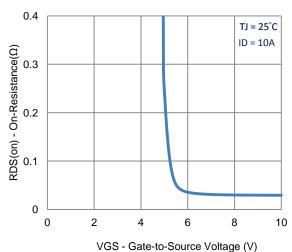
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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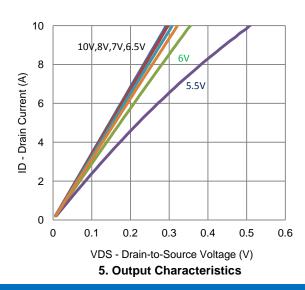
### **Typical Electrical Characteristics**



#### 1. On-Resistance vs. Drain Current



3. On-Resistance vs. Gate-to-Source Voltage

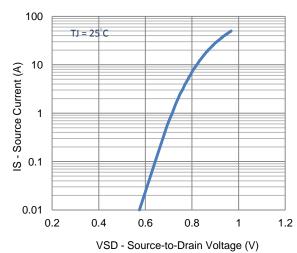


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TJ = 25°C

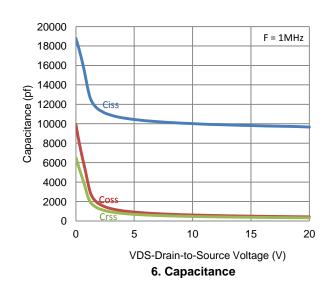
(Y) tuend 10
United 10
0 2 4 6 8

VGS - Gate-to-Source Voltage (V)

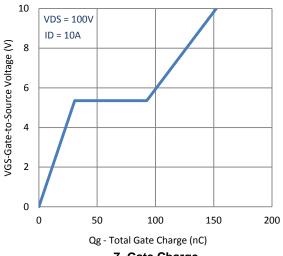
2. Transfer Characteristics



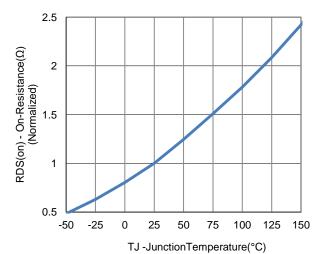
4. Drain-to-Source Forward Voltage



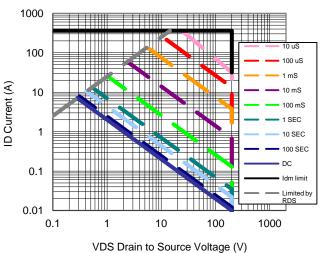
### **Typical Electrical Characteristics**



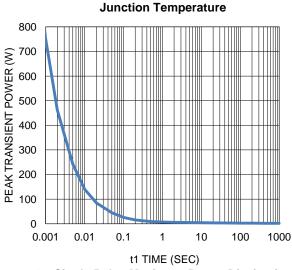
7. Gate Charge



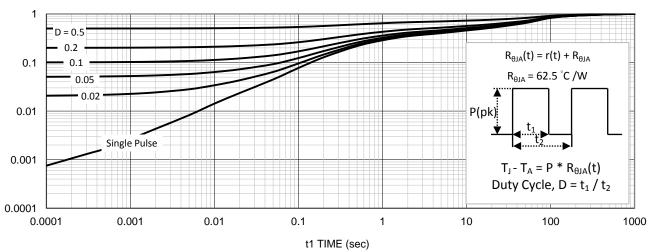
8. Normalized On-Resistance Vs



9. Safe Operating Area



10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

## **Package Information**

